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Dp1-041) Magnetic properties and AC transport measurement of Co ion-implanted ZnO single crystals 김 우철, 손 병철, 박 강순, 강 희재, 오 석근, 신 상원¹, 이 종한¹, 송 종한¹, 노 삼규², 오 상준³, 박 수현³, 김 철성⁴ (충북대학교 물리학과. '한국과학기술연구원. 2한국 표준과학연구원. 3한국기초과학지원연구원. 4국민대 학교 나노 전자물리학과.) We have investigated the magnetic and AC transport properties of Co ion-implanted ZnO single crystals by using high resolution x-ray diffraction (HRXRD), superconducting quantum interference device (SQUID) magnetometer, and physical properties measurement system (PPMS). 0.5 mm thick ZnO (0001) single crystals was prepared, and 80 KeV Co ions with a dose of 3x10¹⁶ cm⁻² were implanted into ZnO at 350 °C. The implanted samples were post-annealed at 700-900 ℃ by rapid thermal annealing (RTA) in N2 atmosphere for 5 min to recrystallize the samples. X-ray diffraction results showed the presence of Co (111) impurities phase in the samples annealed at 700-900 °C. The magnetization curve and temperature dependence of magnetization taken in zero-field-cooling (ZFC) and field-cooling (FC) conditions showed the features of superparamagnetic system due to the presence of magnetic nanoclusters. The blocking temperature (TB) increased with increasing annealing temperature. In electro-transport measurements, resistivity as a function of temperature revealed a typical semiconducting behaviors and showed conduction via variable range hopping (VRH) at low temperature. Magnetoresistance (MR) property at 30 and 50 K, respectively for 800 and 900 °C-annealed samples showed positive MR response (nearly parabolic) centered at H = 0. In AC Hall measurements, anomalous hall effect (AHE) by n-type car-

rier is observed at low temperature.